# Memory FRAM

# 64 K (8 K $\times$ 8) Bit I<sup>2</sup>C

# MB85RC64V

### **■ DESCRIPTION**

The MB85RC64V is an FRAM (Ferroelectric Random Access Memory) chip in a configuration of 8,192 words  $\times$  8 bits, using the ferroelectric process and silicon gate CMOS process technologies for forming the nonvolatile memory cells.

Unlike SRAM, the MB85RC64V is able to retain data without using a data backup battery.

The read/write endurance of the nonvolatile memory cells used for the MB85RC64V has improved to be at least 10<sup>12</sup> cycles, significantly outperforming other nonvolatile memory products in the number.

The MB85RC64V does not need a polling sequence after writing to the memory such as the case of Flash memory or E²PROM.

### **■ FEATURES**

• Bit configuration : 8,192 words × 8 bits

Two-wire serial interface : Fully controllable by two ports: serial clock (SCL) and serial data (SDA).

Operating frequency : 1 MHz (Max)
 Read/write endurance : 10<sup>12</sup> times / byte

• Data retention : 10 years ( + 85 °C), 95 years ( + 55 °C), over 200 years ( + 35 °C)

Operating power supply voltage: 3.0 V to 5.5 V

• Low-power consumption : Operating power supply current 90  $\mu A$  (Typ @1 MHz)

Standby current 5 µA (Typ)

· Operation ambient temperature range

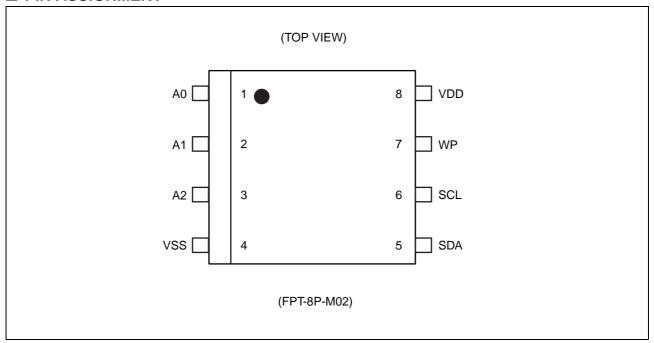
:  $-40~^{\circ}\text{C}$  to  $+85~^{\circ}\text{C}$ 

• Package : 8-pin plastic SOP (FPT-8P-M02)

RoHS compliant



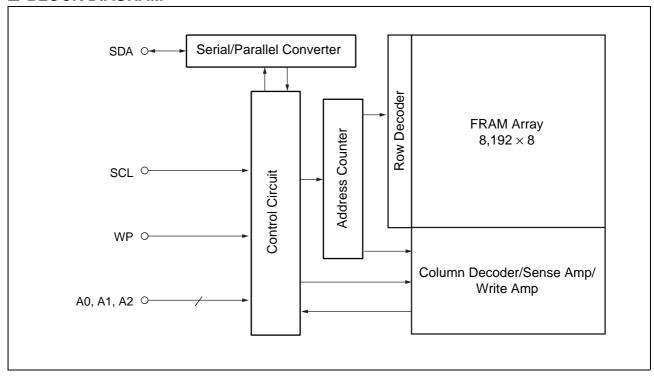
### **■ PIN ASSIGNMENT**



### **■ PIN FUNCTIONAL DESCRIPTIONS**

Pin Number	Pin Name	Functional Description
1 to 3	A0 to A2	Device Address pins The MB85RC64V can be connected to the same data bus up to 8 devices. Device addresses are used in order to identify each of these devices. Connect these pins to VDD pin or VSS pin externally. Only if the combination of VDD and VSS pins matches a Device Address Code inputted from the SDA pin, the device operates. In the open pin state, A0, A1 and A2 pins are internally pulled-down and recognized as the "L" level.
4	VSS	Ground pin
5	SDA	Serial Data I/O pin This is an I/O pin which performs bidirectional communication for both memory address and writing/reading data. It is possible to connect multiple devices. It is an open drain output, so a pull-up resistor is required to be connected to the external circuit.
6	SCL	Serial Clock pin This is a clock input pin for input/output serial data. Data is sampled on the rising edge of the clock and output on the falling edge.
7	WP	Write Protect pin When the Write Protect pin is the "H" level, the writing operation is disabled. When the Write Protect pin is the "L" level, the entire memory region can be overwritten. The reading operation is always enabled regardless of the Write Protect pin input level. The Write Protect pin is internally pulled down to VSS pin, and that is recognized as the "L" level (write enabled) when the pin is the open state.
8	VDD	Supply Voltage pin

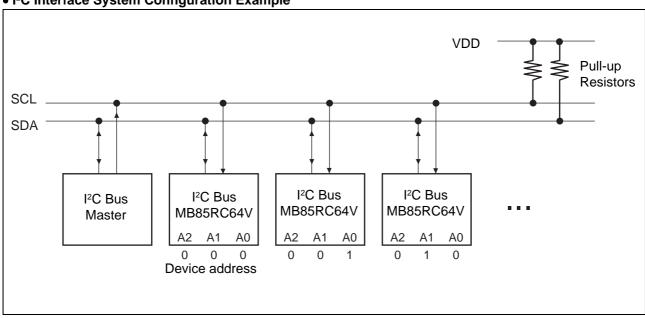
### **■ BLOCK DIAGRAM**



### ■ I<sup>2</sup>C (Inter-Integrated Circuit)

The MB85RC64V has the two-wire serial interface; the I²C bus, and operates as a slave device. The I²C bus defines communication roles of "master" and "slave" devices, with the master side holding the authority to initiate control. Furthermore, an I²C bus connection is possible where a single master device is connected to multiple slave devices in a party-line configuration. In this case, it is necessary to assign a unique device address to the slave device, the master side starts communication after specifying the slave to communicate by addresses.

### • I<sup>2</sup>C Interface System Configuration Example



## MB85RC64V

#### ■ I<sup>2</sup>C COMMUNICATION PROTOCOL

The I<sup>2</sup>C bus is a two wire serial interface that uses a bidirectional data bus (SDA) and serial clock (SCL). A data transfer can only be initiated by the master, which will also provide the serial clock for synchronization. The SDA signal should change while the SCL is the "L" level. However, as an exception, when starting and stopping communication sequence, the SDA is allowed to change while the SCL is the "H" level.

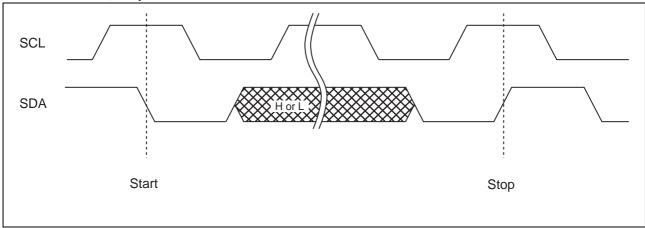
#### Start Condition

To start read or write operations by the I<sup>2</sup>C bus, change the SDA input from the "H" level to the "L" level while the SCL input is in the "H" level.

### • Stop Condition

To stop the I<sup>2</sup>C bus communication, change the SDA input from the "L" level to the "H" level while the SCL input is in the "H" level. In the reading operation, inputting the stop condition finishes reading and enters the standby state. In the writing operation, inputting the stop condition finishes inputting the rewrite data and enters the standby state.

### • Start Condition, Stop Condition



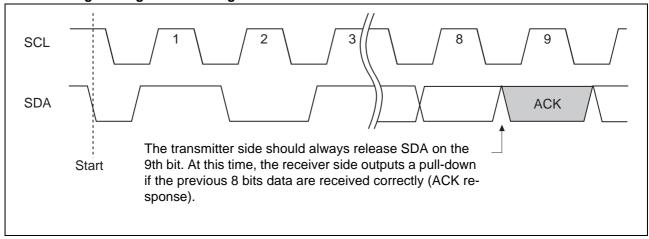
Note: At the write operation, the FRAM device does not need the programming wait time (twc) after issuing the Stop Condition.

### ■ ACKNOWLEDGE (ACK)

In the I<sup>2</sup>C bus, serial data including address or memory information is sent in units of 8 bits. The acknowledge signal indicates that every 8 bits of the data is successfully sent and received. The receiver side usually outputs the "L" level every time on the 9th SCL clock after each 8 bits are successfully transmitted and received. On the transmitter side, the bus is temporarily released to Hi-Z every time on this 9th clock to allow the acknowledge signal to be received and checked. During this Hi-Z released period, the receiver side pulls the SDA line down to indicate the "L" level that the previous 8 bits communication is successfully received.

In case the slave side receives Stop condition before sending or receiving the ACK "L" level, the slave side stops the operation and enters to the standby state. On the other hand, the slave side releases the bus state after sending or receiving the NACK "H" level. The master side generates Stop condition or Start condition in this released bus state.

### Acknowledge timing overview diagram



## MB85RC64V

### **■** DEVICE ADDRESS WORD (Slave address)

Following the start condition, the master sends the 8 bits device address word to start I<sup>2</sup>C communication. The device address word (8 bits) consists of a device Type code (4 bits), device address code (3 bits), and a read/write code (1 bit).

### • Device Type Code (4 bits)

The upper 4 bits of the device address word are a device type code that identifies the device type, and are fixed at "1010" for the MB85RC64V.

### • Device Address Code (3 bits)

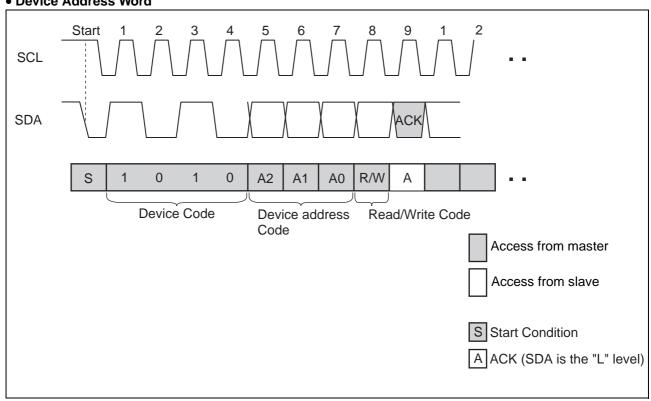
Following the device type code, the 3 bits of the device address code are input in order of A2, A1 and A0. The device address code identifies one device from up to eight devices connected to the bus. Each MB85RC64V is given a unique 3 bits code on the device address pin (external hardware pin A2, A1 and A0). The slave only responds if the received device address code is equal to this unique 3 bits code.

#### • Read/Write Code (1 bit)

The 8th bit of the device address word is the R/W (read/write) code. When the R/W code is "0", a write operation is enabled, and the R/W code is "1", a read operation is enabled for the MB85RC64V.

It turns to a stand-by state if the device code is not "1010" or device address code does not equal to pins A2, A1 and A0.

#### Device Address Word



#### **■ DATA STRUCTURE**

In the  $I^2C$  bus, the acknowledge "L" level is output on the 9th bit by a slave, after the 8 bits of the device address word following the start condition are input by a master. After confirming the acknowledge response by the master, the master outputs 8 bits  $\times$  2 memory address to the slave. When the each memory address input ends, the slave again outputs the acknowledge "L" level. After this operation, the I/O data follows in units of 8 bits, with the acknowledge "L" level output after every 8 bits.

It is determined by the R/W code whether the data line is driven by the master or the slave. However, the clock line shall be driven by the master. For a write operation, the slave will accept 8 bits from the master, then send an acknowledge. If the master detects the acknowledge, the master will transfer the next 8 bits. For a read operation, the slave will place 8 bits on the data line, then wait for an acknowledge from the master.

#### ■ FRAM ACKNOWLEDGE -- POLLING NOT REQUIRED

The MB85RC64V performs the high speed write operations, so any waiting time for an ACK polling\* does not occur.

\*: In E<sup>2</sup>PROM, the Acknowledge Polling is performed as a progress check whether rewriting is executed or not. It is normal to judge by the 9th bit of Acknowledge whether rewriting is performed or not after inputting the start condition and then the device address word (8 bits) during rewriting.

### **■** WRITE PROTECT (WP)

The entire memory array can be write protected using the Write Protect pin. When the Write Protect pin is set to the "H" level, the entire memory array will be write protected. When the Write Protect pin is the "L" level, the entire memory array will be rewritten. Reading is allowed regardless of the WP pin's "H" level or "L" level.

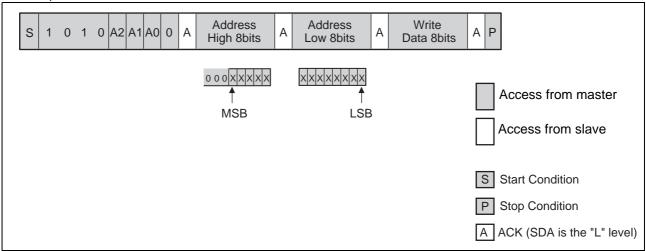
Note: The Write Protect pin is pulled down internally to the VSS pin, therefore if the Write Protect pin is open, the pin status is detected as the "L" level (write enabled).

## MB85RC64V

#### **■ COMMAND**

• Byte Write

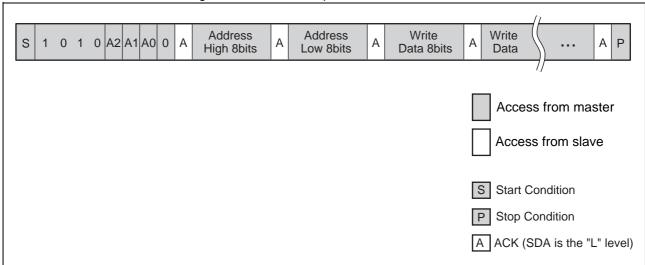
If the device address word (R/W "0" input ) is sent following the start condition, the slave responds with an ACK. After this ACK, write addresses and data are sent in the same way, and the write ends by generating a stop condition at the end.



Note: In the MB85RC64V, input "000" to the upper 3 bits of the MSB because the address is expressed with 13 bits.

### • Page Write

If additional 8 bits are continuously sent after the same command (except stop condition) as Byte Write, a page write is performed. The memory address rolls over to first memory address (0000H) at the end of the address. Therefore, if more than 8 Kbytes are sent, the data is overwritten in order starting from the start of the memory address that was written first. Because FRAM performs the high-speed write operations, the data will be written to FRAM right after the ACK response finished.



Note: It is not necessary to take a period for internal write operation cycles from the buffer to the memory after the stop condition is generated.

#### · Current Address Read

When the previous write or read operation finishes successfully up to the stop condition and assumes the last accessed address is "n", then the address at "n+1" is read by sending the following command unless turning the power off. If the memory address is last address, the address counter will roll over to 0000H. The current address in memory address buffer is undefined immediately after the power is turned on.

	Access from master
(n+1) address	Access from slave
S 1 0 1 0 A2 A1 A0 1 A Read Data 8bits N P	S Start Condition
Data obits	P Stop Condition
	A ACK (SDA is the "L" level)
	N NACK (SDA is the "H" level)

#### Random Read

The one byte of data from the memory address saved in the memory address buffer can be read out synchronously to SCL by specifying the address in the same way as for a write, and then issuing another start condition and sending the Device Address Word (R/W "1" input).

The final NACK (SDA is the "H" level) is issued by the receiver that receives the data. In this case, this bit is issued by the master side.

S 1	0	1	0 A2	2 A1	A0	0	А	Address High 8bits	A	Address Low 8bits	A	S	1	0	1	0 A2	A1 A0 1	A	Read Data 8bits	N P
																	Acces	s fro	om master	
																	Acces	s fro	m slave	
																S	Start C	ondi	ition	
																Р	Stop C	ondi	tion	
																Α	ACK (S	SDA i	is the "L" lev	vel)
																N	NACK	(SD/	A is the "H"	level)

# MB85RC64V

### · Sequential Read

Data can be received continuously following the Device address word (R/W "1" input) after specifying the address in the same way as for Random Read. If the read reaches the end of address, the internal read address automatically rolls over to first memory address 0000H and keeps reading.

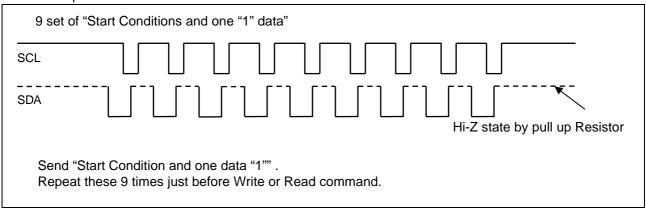
 A Read Data 8bits A Read Data N P	
1/	
Access from maste	er
Access from slave	
P Stop Condition	
A ACK (SDA is the "L"	level)
N NACK (SDA is the "H	ł" level)

### ■ SOFTWARE RESET SEQUENCE OR COMMAND RETRY

In case the malfunction has occurred after power on, the master side stopped the I<sup>2</sup>C communication during processing, or unexpected malfunction has occurred, execute the following (1) software recovery sequence just before each command, or (2) retry command just after failure of each command.

### (1) Software Reset Sequence

Since the slave side may be outputting "L" level, do not force to drive "H" level, when the master side drives the SDA port. This is for preventing a bus conflict. The additional hardware is not necessary for this software reset sequence.



### (2) Command Retry

Command retry is useful to recover from failure response during I<sup>2</sup>C communication.

### ■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Ra	Unit		
raidilletei	Symbol	Min	Max	Oilit	
Power supply voltage*	V <sub>DD</sub>	- 0.5	+ 6.0	V	
Input voltage*	Vin	- 0.5	$V_{DD} + 0.5 \ (\le 6.0)$	V	
Output voltage*	Vouт	- 0.5	$V_{DD} + 0.5 \ (\le 6.0)$	V	
Operation ambient temperature	TA	- 40	+ 85	°C	
Storage temperature	Tstg	<b>- 55</b>	+ 125	°C	

<sup>\*:</sup> These parameters are based on the condition that VSS is 0 V.

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

### ■ RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol		Unit		
Farameter	Зушьог	Min	Тур	Max	Offic
Power supply voltage*1	$V_{DD}$	3.0	_	5.5	V
Operation ambient temperature*2	TA	- 40	_	+ 85	°C

<sup>\*1:</sup> These parameters are based on the condition that VSS is 0 V.

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure. No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their representatives beforehand.

<sup>\*2:</sup> Ambient temperature when only this device is working. Please consider it to be the almost same as the package surface temperature.

# MB85RC64V

### **■ ELECTRICAL CHARACTERISTICS**

### 1. DC Characteristics

(within recommended operating conditions)

Parameter	Symbol	Condition		Value		Unit
Farameter	Syllibol	Condition	Min	Тур	Max	
Input leakage current*1	ILI	$V_{IN} = 0 V to V_{DD}$	_	_	1	μΑ
Output leakage current*2	ILO	Vout = 0 V to VDD	_	_	1	μΑ
Operating power supply	IDD	SCL = 400 kHz	_	40	80	μΑ
current	IDD	SCL = 1000 kHz	_	90	130	μΑ
Standby current	İsa	SCL, SDA = $V_{DD}$ WP = 0 V or $V_{DD}$ or Open Under Stop Condition $T_A = +25$ °C	_	5	10	μΑ
"H" level input voltage	ViH	$V_{DD} = 3.0 \text{ V to } 5.5 \text{ V}$	$V_{DD} \times 0.8$	_	5.5	V
"L" level input voltage	Vıl	$V_{DD} = 3.0 \text{ V to } 5.5 \text{ V}$	Vss	_	$V_{DD} \times 0.2$	V
"L" level output voltage	Vol	lol = 3 mA	_	_	0.4	V
Input resistance for	D	VIN = VIL (Max)	50	_	_	kΩ
WP, A0, A1, and A2 pins	Rin	VIN = VIH (Min)	1	_	_	MΩ

\*1: Applicable pin: SCL,SDA

\*2: Applicable pin: SDA

### 2. AC Characteristics

		Value						
Parameter	Symbol		DARD DE	FAST	MODE	FAST MODE PLUS		Unit
		Min	Max	Min	Max	Min	Max	
SCL clock frequency	FSCL	0	100	0	400	0	1000	kHz
Clock high time	Тнідн	4000		600	_	400		ns
Clock low time	TLOW	4700		1300		600		ns
SCL/SDA rising time	Tr		1000		300		300	ns
SCL/SDA falling time	Tf		300		300		100	ns
Start condition hold	THD:STA	4000		600	_	250		ns
Start condition setup	Tsu:sta	4700		600		250		ns
SDA input hold	THD:DAT	20		20		20		ns
SDA input setup	T <sub>SU:DAT</sub>	250		100	_	100		ns
SDA output hold	T <sub>DH:DAT</sub>	0		0		0		ns
Stop condition setup	Тѕи:ѕто	4000		600		250		ns
SDA output access after SCL falling	Таа		3000		900		550	ns
Pre-charge time	T <sub>BUF</sub>	4700	_	1300	_	500	_	ns
Noise suppression time (SCL and SDA)	Tsp	_	50	_	50	_	50	ns

AC characteristics were measured under the following measurement conditions.

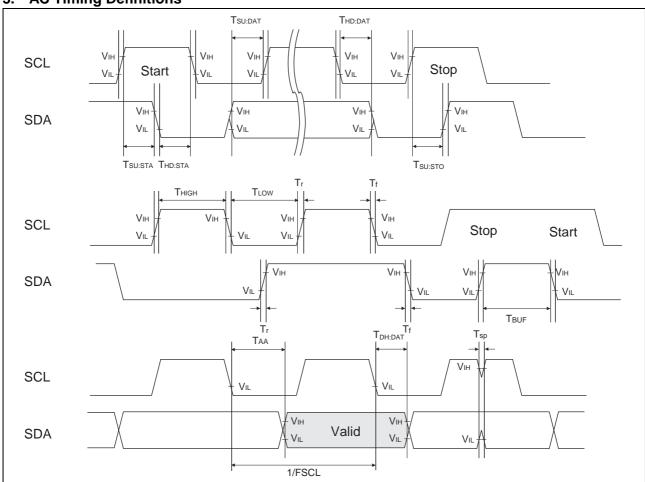
Power supply voltage : STANDARD MODE and FAST MODE 3.0 V to 5.5 V

: FAST MODE PLUS 4.5 V to 5.5 V

Operation ambient temperature  $: -40 \, ^{\circ}\text{C}$  to  $+85 \, ^{\circ}\text{C}$ Input voltage magnitude  $: V_{\text{DD}} \times 0.2$  to  $V_{\text{DD}} \times 0.8$ 

Input rising time : 5 ns
Input falling time : 5 ns
Input judge level : VDD/2
Output judge level : VDD/2

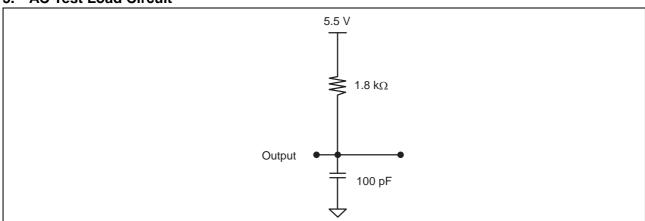
### 3. AC Timing Definitions



### 4. Pin Capacitance

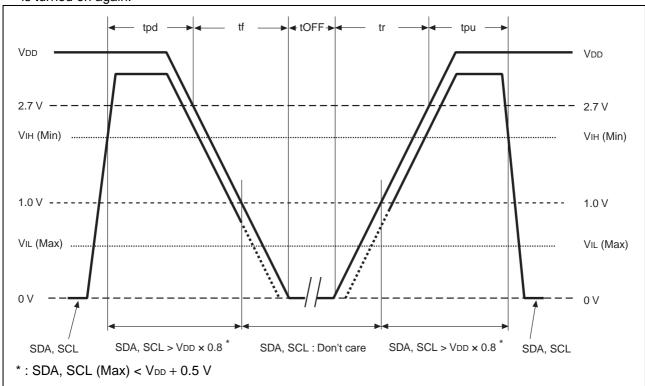
Parameter	Symbol	Conditions		Value		Unit
Farameter	Symbol	Conditions	Min	Тур	Max	Oilit
I/O capacitance	C <sub>I/O</sub>	$V_{DD} = V_{IN} = V_{OUT} = 0 V$ ,	_	_	15	pF
Input capacitance	Cin	$f = 1 \text{ MHz}, T_A = +25 ^{\circ}\text{C}$		_	15	pF

### 5. AC Test Load Circuit



### **■ POWER ON/OFF SEQUENCE**

If  $V_{DD}$  falls down below 2.0V,  $V_{DD}$  is required to be started from 0V to prevent malfunctions when the power is turned on again.



Parameter	Symbol	Va	lue	Unit	Condition
raiametei	Syllibol	Min	Max	Oilit	Condition
SDA, SCL level hold time during power down	tpd	85	_	ns	_
SDA, SCL level hold time during	tou	85	_	ns	$V_{DD} = 5.0V \pm 0.5V$ Operation
power up	tpu	0.5		ms	V <sub>DD</sub> = 3.3V ± 0.3V Operation
Power supply rising time	tr	0.5	50	me	$V_{DD} = 5.0V \pm 0.5V$ Operation
Power supply fishing time	u	0.005	50	ms	V <sub>DD</sub> = 3.3V ± 0.3V Operation
Power supply falling time	tf	0.5	50	ms	_
Power off time	tOFF	50		ms	_

If the device does not operate within the specified conditions of read cycle, write cycle or power on/off sequence, memory data can not be guaranteed.

### **■ FRAM CHARACTERISTICS**

Item	Min	Max	Unit	Parameter
Read/Write Endurance*1	10 <sup>12</sup>	_	Times/byte	Operation Ambient Temperature T <sub>A</sub> = +85 °C
	10	_		Operation Ambient Temperature T <sub>A</sub> = +85 °C
Data Retention*2	95	_	Years	Operation Ambient Temperature T <sub>A</sub> = +55 °C
	≥ 200	_		Operation Ambient Temperature T <sub>A</sub> = +35 °C

<sup>\*1:</sup> Total number of reading and writing defines the minimum value of endurance, as an FRAM memory operates with destructive readout mechanism.

### **■ NOTE ON USE**

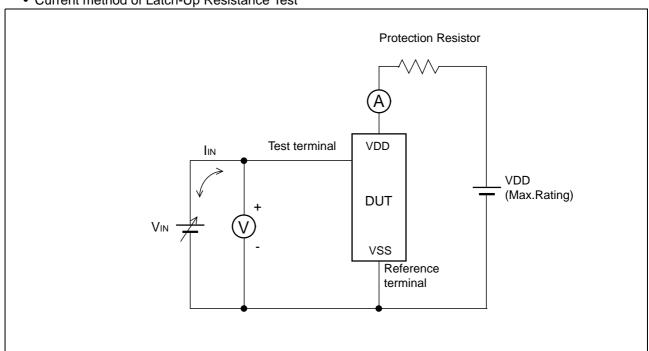
- We recommend programming of the device after reflow. Data written before reflow cannot be guaranteed.
- During the access period from the start condition to the stop condition, keep the level of WP, A0, A1 and A2 pins to the "H" level or the "L" level.
- If the time lag between STOP CONDITION and START CONDITION is long, it is rarely but, in some cases, that device will ignore the first START CONDITION. When the device responds with unpredictable signals, execute one of the following from the master side.
  - (1) Software Reset
  - (2) A part of software reset (one start condition and data "1")
  - (3) Retry the same command (Command Retry)

<sup>\*2 :</sup> Minimum values define retention time of the first reading/writing data right after shipment, and these values are calculated by qualification results.

### **■ ESD AND LATCH-UP**

Test	DUT	Value
ESD HBM (Human Body Model) JESD22-A114 compliant		≥  2000 V
ESD MM (Machine Model) JESD22-A115 compliant		≥  200 V
ESD CDM (Charged Device Model) JESD22-C101 compliant		≥  1000 V
Latch-Up (I-test) JESD78 compliant	MB85RC64VPNF-G-JNE1	_
Latch-Up (V <sub>supply</sub> overvoltage test) JESD78 compliant		_
Latch-Up (Current Method) Proprietary method		_
Latch-Up (C-V Method) Proprietary method		≥  200 V

• Current method of Latch-Up Resistance Test

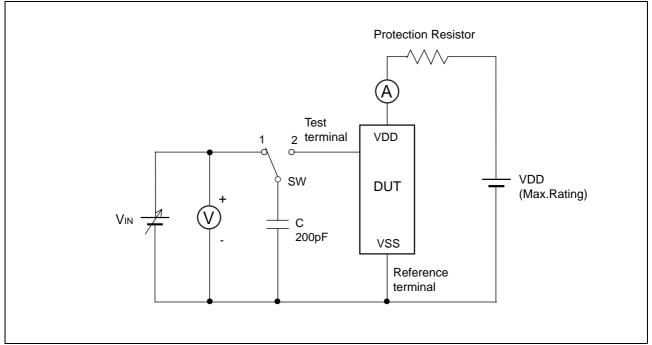


Note: The voltage  $V_{IN}$  is increased gradually and the current  $I_{IN}$  of 300 mA at maximum shall flow. Confirm the latch up does not occur under  $I_{IN}=\pm300$  mA.

In case the specific requirement is specified for I/O and  $I_{IN}$  cannot be 300 mA, the voltage shall be increased to the level that meets the specific requirement.

# MB85RC64V

### • C-V method of Latch-Up Resistance Test



Note: Charge voltage alternately switching 1 and 2 approximately 2 sec interval. This switching process is considered as one cycle.

Repeat this process 5 times. However, if the latch-up condition occurs before completing 5 times, this test must be stopped immediately.

### ■ REFLOW CONDITIONS AND FLOOR LIFE

[ JEDEC MSL ] : Moisture Sensitivity Level 3 (ISP/JEDEC J-STD-020D)

### **■ CURRENT STATUS ON CONTAINED RESTRICTED SUBSTANCES**

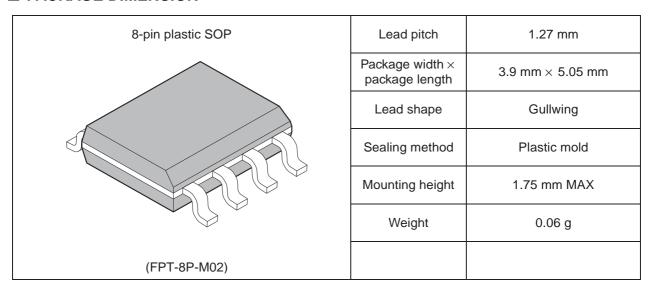
This product complies with the regulations of REACH Regulations, EU RoHS Directive and China RoHS.

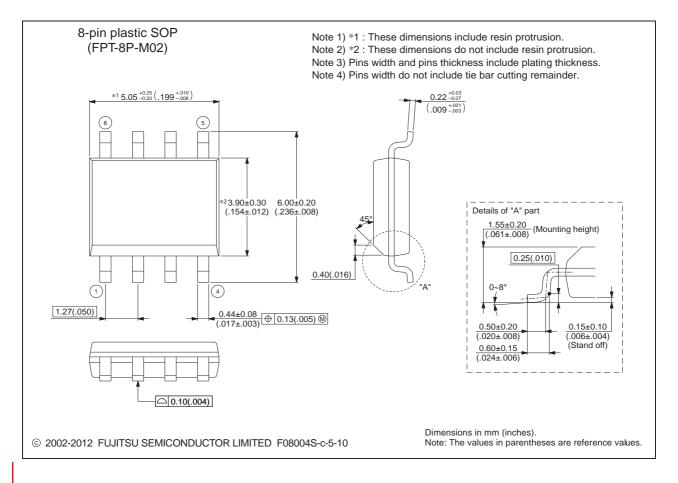
### **■ ORDERING INFORMATION**

Part number	Package	Shipping form	Minimum shipping quantity
MB85RC64VPNF-G-JNE1	8-pin, plastic SOP (FPT-8P-M02)	Tube	*
MB85RC64VPNF-G-JNERE1	8-pin, plastic SOP (FPT-8P-M02)	Embossed Carrier tape	1500

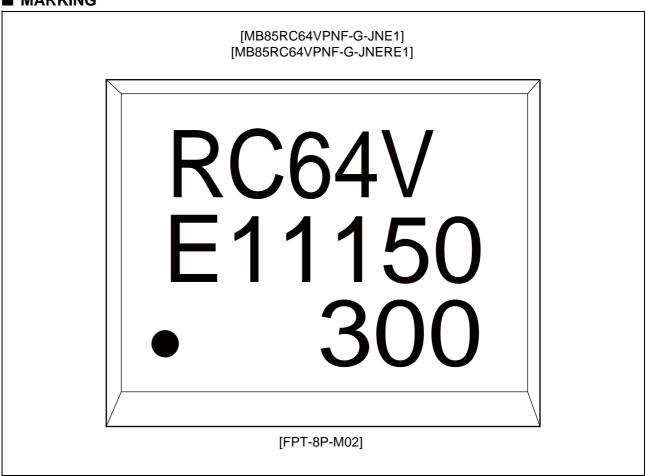
<sup>\*:</sup> Please contact our sales office about minimum shipping quantity.

### **■ PACKAGE DIMENSION**





### **■ MARKING**

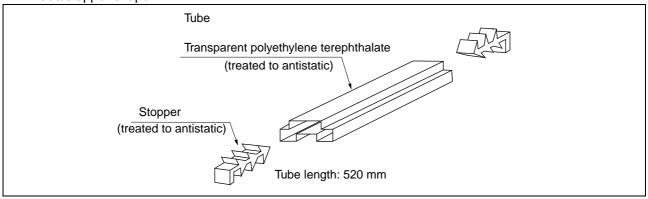


### **■ PACKING INFORMATION**

### 1. Tube

### 1.1 Tube Dimensions

• Tube/stopper shape

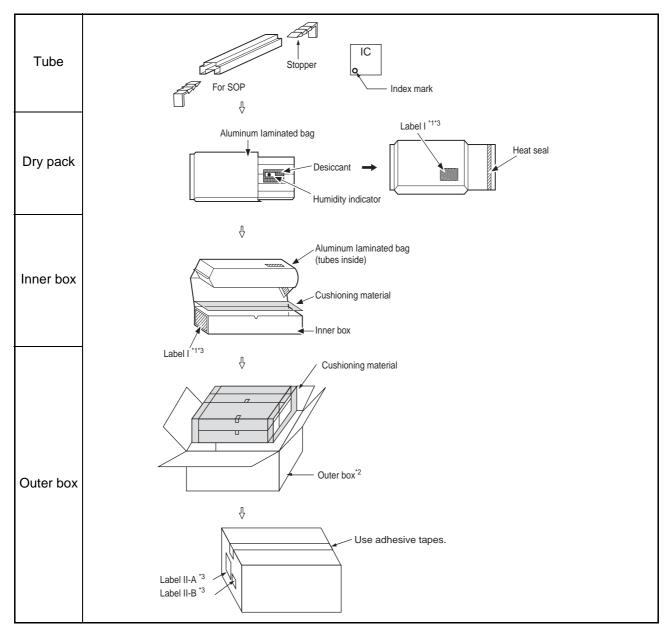


### **Tube cross-sections and Maximum quantity**

		Maximum quantity			
Package form	Package code	pcs/ tube	pcs/inner box	pcs/outer box	
SOP, 8, plastic (2)	FPT-8P-M02	95	7600	30400	
7.4 6.4 8.4 9.7 7.4					
©2006-2010 FUJITSU SEMICONDUCTOR LIMITED F08008-SET1-PET:FJ99L-0022-E0008-1-K-3					
t = 0.5 Transparent polyethylene terephthalate					

(Dimensions in mm)

### 1.2 Tube Dry pack packing specifications



<sup>\*1:</sup> For a product of witch part number is suffixed with "E1", a " [G] (N)" marks is display to the moisture barrier bag and the inner boxes.

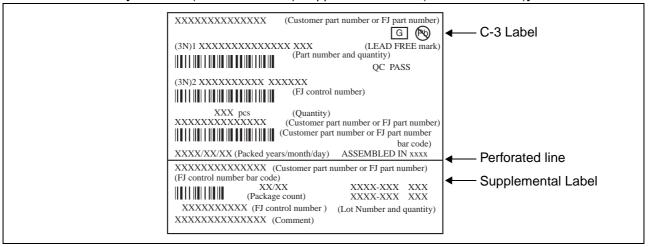
Note: The packing specifications may not be applied when the product is delivered via a distributor.

<sup>\*2:</sup> The space in the outer box will be filled with empty inner boxes, or cushions, etc.

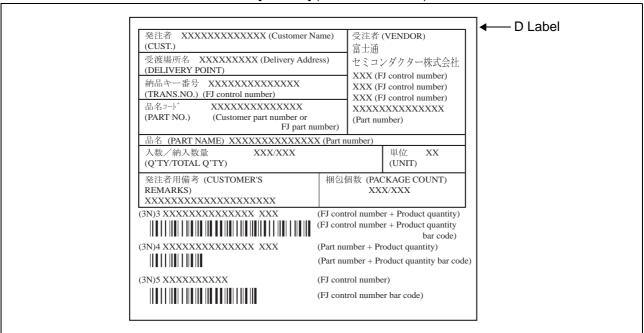
<sup>\*3:</sup> Please refer to an attached sheet about the indication label.

#### 1.3 Product label indicators

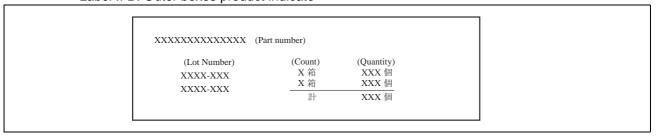
Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping) [C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]



Label II-A: Label on Outer box [D Label] (100mm × 100mm)



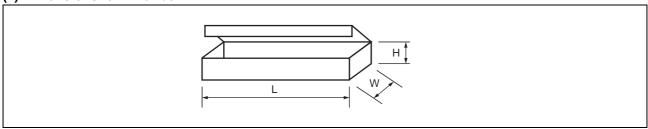
Label II-B: Outer boxes product indicate



Note: Depending on shipment state, "Label II-A" and "Label II-B" on the external boxes might not be printed.

### 1.4 Dimensions for Containers

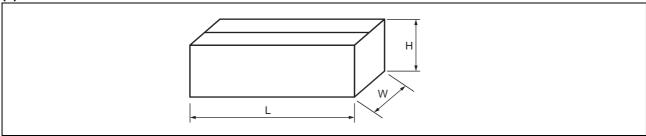
### (1) Dimensions for inner box



L	W	Н
540	125	75

(Dimensions in mm)

### (2) Dimensions for outer box



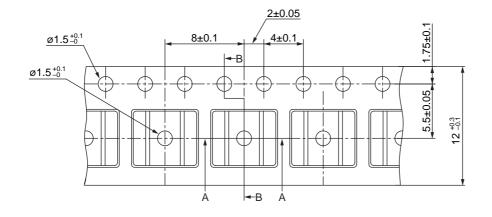
L	W	Н
565	270	180

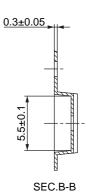
(Dimensions in mm)

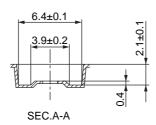
### 2. Emboss Tape

### 2.1 Tape Dimensions

PKG code	Reel No	Maxim	um storage ca	apacity
1110 0000	1100.110	pcs/reel	pcs/outer box	
FPT-8P-M02	3	1500	1500	10500







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(Dimensions in mm)

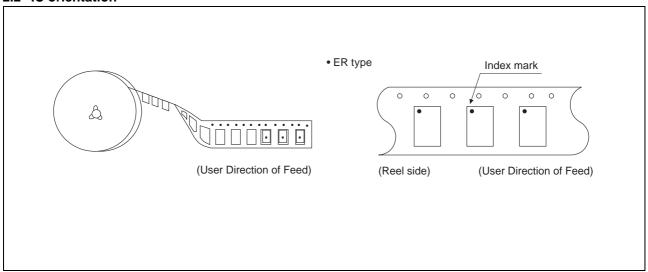
Material: Conductive polystyrene

Heat proof temperature : No heat resistance.

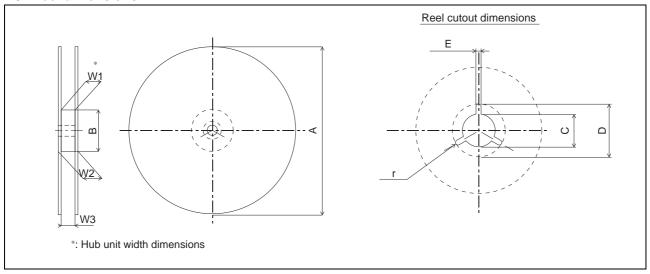
Package should not be baked

by using tape and reel.

### 2.2 IC orientation



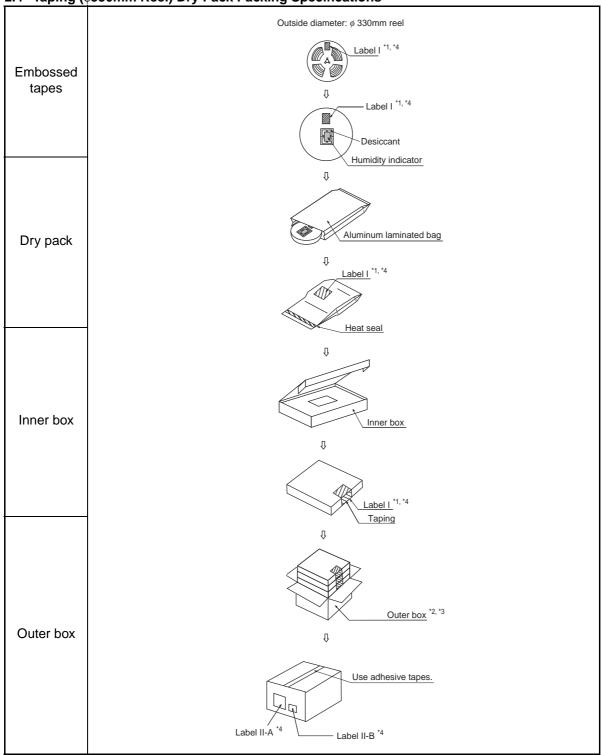
### 2.3 Reel dimensions



#### Dimensions in mm

															-
Reel No	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
Tape width Symbol	8	1	2	1	16 24			3	2	44 56		12	16	24	
Α	254 ± 2	254 ± 2	330 ± 2	254 ± 2	$330 \pm 2$	254 ± 2	$330 \pm 2$				330	± 2			
В				1	00 -0			100 -0	150 +2	100 +2	150 -2	100 -2	100 ± 2		
С		$13 \pm 0.2$ $13^{+0.5}_{-0.2}$													
D		21 ± 0.8 20.5 <sup>+1</sup> <sub>-0.2</sub>													
Е								$2 \pm 0.5$							
W1	8.4 $^{+2}_{.0}$ 12.4 $^{+2}_{.0}$ 16.4 $^{+2}_{.0}$ 24.4 $^{+2}_{.0}$ 32.4 $^{+2}_{.0}$ 44.4 $^{+2}_{.0}$ 56.4 $^{+2}_{.0}$					12.4 +1	16.4 +1	24.4+0.1							
W2						less than 62.4	less than 18.4	less than 22.4	less than 30.4						
W3	7.9 ~ 10.9	11.9	~ 15.4	15.9	~ 19.4	23.9	~ 27.4	7.4 31.9 ~ 35.4			~ 47.4	55.9 ~ 59.4	12.4 ~ 14.4	16.4 ~ 18.4	24.4 ~ 26.4
r		1.0													





<sup>\*1:</sup> For a product of witch part number is suffixed with "E1", a " G (R)" marks is display to the moisture barrier bag and the inner boxes.

Note: The packing specifications may not be applied when the product is delivered via a distributor.

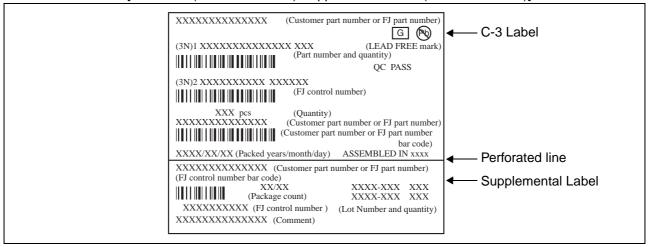
<sup>\*2:</sup> The size of the outer box may be changed depending on the quantity of inner boxes.

<sup>\*3:</sup> The space in the outer box will be filled with empty inner boxes, or cushions, etc.

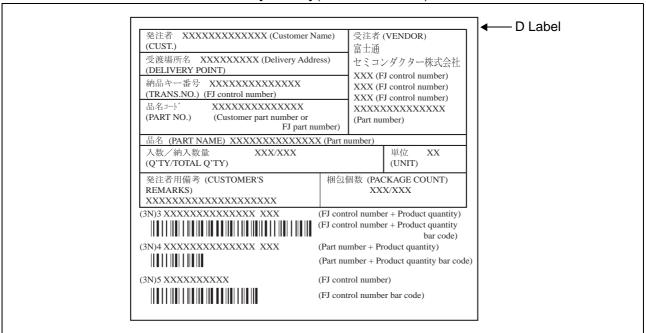
<sup>\*4:</sup> Please refer to an attached sheet about the indication label.

#### 2.5 Product label indicators

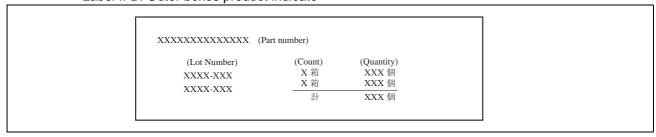
Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping) [C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]



Label II-A: Label on Outer box [D Label] (100mm × 100mm)



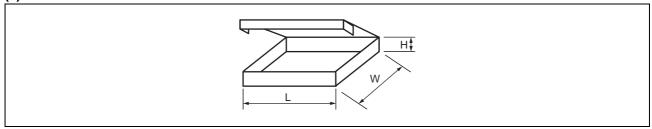
Label II-B: Outer boxes product indicate



Note: Depending on shipment state, "Label II-A" and "Label II-B" on the external boxes might not be printed.

### 2.6 Dimensions for Containers

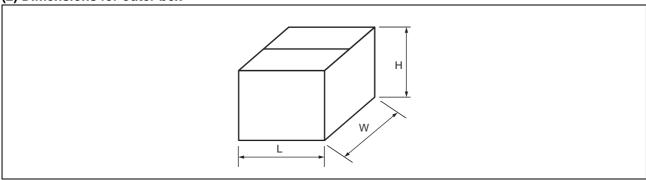
### (1) Dimensions for inner box



Tape width	L	W	Н
12, 16	365		40
24, 32		345	50
44		343	65
56			75

(Dimensions in mm)

### (2) Dimensions for outer box



L	W	Н
415	400	315

(Dimensions in mm)

### ■ MAJOR CHANGES IN THIS EDITION

A change on a page is indicated by a vertical line drawn on the left side of that page.

Page	Section	Change Results
11	■ RECOMMENDED OPERATING CONDITIONS	Added note on the Operation Ambient Temperature.  Moved the "High Level Input Voltage" and "Low Level Input Voltage" to DC Characteristics.
12	1. DC Characteristics	Moved the "High Level Input Voltage" and "Low Level Input Voltage" from RECOMMENDED OPERATING CONDITIONS.
18	CURRENT STATUS ON CONTAINED RESTRICTED SUBSTANCES	Deleted the URL info.
20	■ PACKAGE DIMENSION	Deleted the URL info.

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